

P-Channel 100-V (D-S) MOSFET

r-Channel	100-V	(D-9)	INIOSE	_ I

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 100	0.18 at V _{GS} = - 10 V	- 3	7.9		
- 100	0.2 at V _{GS} = - 4.5 V	-2.8	7.9		

FEATURES

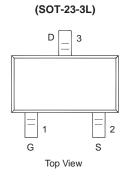
- DT-Trench Power MOSFET
- Ultra Low On-Resistance
- 100 % R_g Tested 100 % UIS Tested

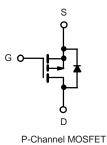


COMPLIANT

APPLICATIONS

• Active Clamp Circuits in DC/DC Power Supplies





ABSOLUTE MAXIMUM RATINGS T	$_{A}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 100		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	I _D	- 3.8	- 3	
	T _A = 70 °C		- 2.5	- 2.8	
Pulsed Drain Current		I _{DM}	- 10.6		Α
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 5	- 6.8	
Single Pulse Avalanche Current	L = 1.0 mH	I _{AS}	4.5		
Single Pulse Avalanche Energy	L = 1.0 mm	E _{AS}		1.01	mJ
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	P _D	1.25 0.75 0.8 0.48		W
	T _A = 70 °C	' D			v V
Operating Junction and Storage Temperature Rang	e	T _J , T _{stg}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	D	75	100	
	Steady State	R_{thJA}	120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50]

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 100			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.2		- 2.5		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	l	V _{DS} = - 150 V, V _{GS} = 0 V	- 150 V, V _{GS} = 0 V		- 1		
	IDSS	V _{DS} = - 150 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 2.6			Α	
5	В	$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	0.18				
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 0.5 A		0.2		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 0.5 A		2.2		S	
Diode Forward Voltage	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		0.7	- 1.2	V	
Dynamic ^b			•				
Total Gate Charge	Q_g	V 75 V V 10 V		7.7	12		
Gate-Source Charge	Q _{gs}	$V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$		1.5		nC	
Gate-Drain Charge	Q_{gd}	1 _D = 0.0 /1		2.5			
Gate Resistance	R_g	f = 1.0 MHz		9		Ω	
Input Capacitance	C _{iss}			340	510		
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		30		pF	
Reverse Transfer Capacitance	C _{rss}			16			
Switching ^c							
T	t _{d(on)}	V 75 V B 75 0		7	11		
Turn-On Time	t _r	$V_{DD} = -75 \text{ V, } R_L = 75 \Omega$ $I_D \cong -1.0 \text{ A, } V_{GEN} = -10 \text{ V}$		11	17	ns	
Turn-Off Time	t _{d(off)}	$R_{a} = 6 \Omega$		16	25	113	
	t _f	. ·y =		11	17		
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		90	135	nC	

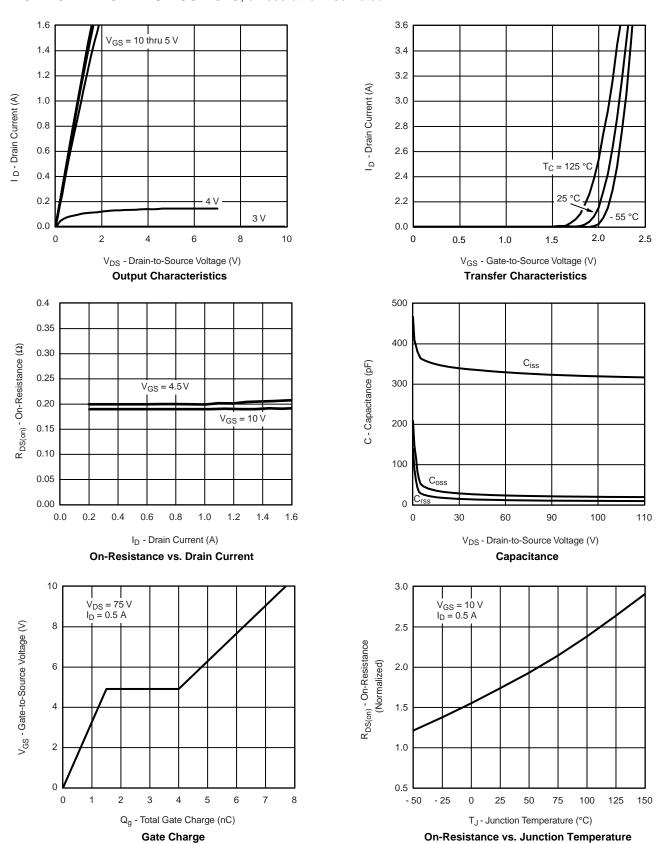
Notes:

- a. Pulse test: PW \leq 300 µs duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

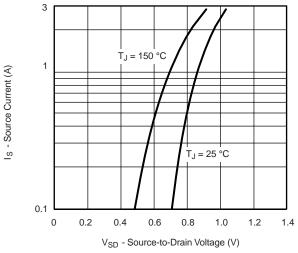


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

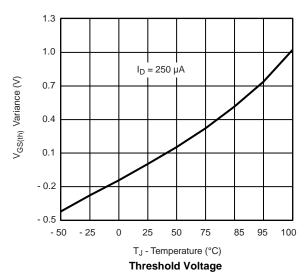


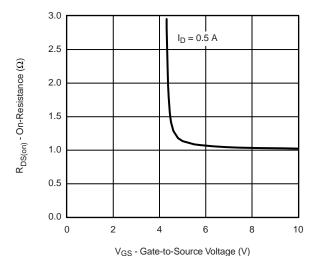


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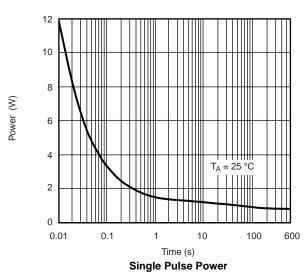


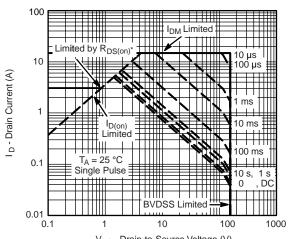
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



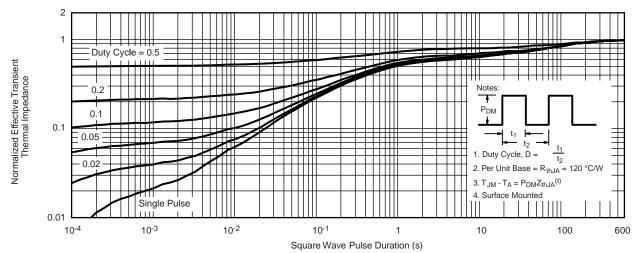


 $V_{DS} \mbox{ - Drain-to-Source Voltage (V)} \\ ^*V_{GS} \mbox{ > minimum } V_{GS} \mbox{ at which } R_{DS(on)} \mbox{ is specified}$

Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient





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